



NTD14N03R-1G Information



For Reference Only

Part Number NTD14N03R-1G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 25V 2.5A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD14N03R-1G Specifications

Manufacturer Part Number NTD14N03R-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 2.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1.8nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 115pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.04W (Ta), 20.8W (Tc) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds I15pF @ 20V Vgs (Max) ### 20V ### 2	Manufacturer Part Number	NTD14N03R-1G
Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 2.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1.8nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 115pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.04W (Ta), 20.8W (Tc) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer	ON Semiconductor
PackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs1.8nC @ 5VInput Capacitance (Ciss) (Max) @ Vds115pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series - N-Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1.8nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 115pF @ 20V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 1.04W (Ta), 20.8W (Tc) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case Toology (Max) (Pas)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs1.8nC @ 5VInput Capacitance (Ciss) (Max) @ Vds115pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs1.8nC @ 5VInput Capacitance (Ciss) (Max) @ Vds115pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs1.8nC @ 5VInput Capacitance (Ciss) (Max) @ Vds115pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Cate Charge (Qg) (Max) @ Vds 1.04W (Ta), 20.8W (Tc) 95 mOhm @ 5A, 10V Operating Temperature For Cate Charge (Qg) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Input Capacita	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs1.8nC @ 5VInput Capacitance (Ciss) (Max) @ Vds115pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	25V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	2.5A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 115pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 115pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.04W (Ta), 20.8W (Tc)Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	1.8nC @ 5V
FET Feature - Power Dissipation (Max) 1.04W (Ta), 20.8W (Tc) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	115pF @ 20V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 95 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs95 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	1.04W (Ta), 20.8W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	95 mOhm @ 5A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NTD14N03R-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD14N03R-1G Payment Methods



















NTD14N03R-1G Shipping Methods













If you have any question about NTD14N03R-1G, please do not hesitate to contact us!

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